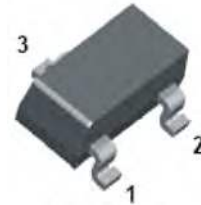
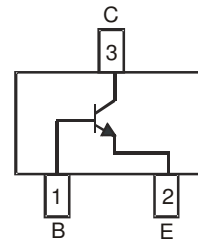


Features

- Low Deviation in Base-Emitter Voltage
- Surface Mount Package
- Ideally Suited for Automated Assembly Processes
- **Lead Free by Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**



SOT-23



Schematic & Pin Configuration

Mechanical Data

- Case: SOT-23
- Case material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	6	V
Output Current - Continuous (Note 3)	I_C	200	mA
Peak Collector Current	I_{CM}	200	mA
Peak Emitter Current	I_{EM}	200	mA
Power Dissipation (Note 3)	P_d	300	mW
Power Deration	P_{der}	2.4	mW/°C

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient Air (Note 3)	$R_{\theta JA}$	417	°C/W
Operating and Storage Junction Temperature Range	T_j, T_{STG}	-55 to +150	°C

- Notes:
1. No purposefully added lead.
 2. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on page 4 or on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics: NPN Transistor @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50	—	—	V	$I_C = 10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	45	—	—	V	$I_C = 1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CEX}	—	—	15	nA	$V_{CE} = 50\text{V}, V_{EB(OFF)} = 3.0\text{V}$
Base Cutoff Current (I_{BEX})	I_{BL}	—	—	15	nA	$V_{CE} = 40\text{V}, V_{EB(OFF)} = 3.0\text{V}$
Collector-Base Cut Off Current	I_{CBO}	—	—	15	nA	$V_{CB} = 40\text{V}, I_E = 0$
				5	μA	$V_{CB} = 30\text{V}, T_A = 150^\circ\text{C}$
Collector-Emitter Cut Off Current, $I_{O(OFF)}$	I_{CEO}	—	—	50	nA	$V_{CE} = 40\text{V}, I_B = 0$
Emitter-Base Cut Off Current	I_{EBO}	—	—	50	nA	$V_{EB} = 5\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 4)						
DC Current Gain	h_{FE}	180	—	—	—	$V_{CE} = 5\text{V}, I_C = 100\mu\text{A}$
		150	—	—	—	$V_{CE} = 5\text{V}, I_C = 500\mu\text{A}$
		220	—	—	—	$V_{CE} = 5\text{V}, I_C = 1\text{mA}$
		220	—	—	—	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$
		150	—	—	—	$V_{CE} = 5\text{V}, I_C = 5\text{mA}$
		150	—	—	—	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.09	0.18	V	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$
		—	0.2	0.4	V	$I_C = 100\text{mA}, I_B = 5\text{mA}$
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	647	657	667	mV	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	0.8	V	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$
		—	—	0.9	V	$I_C = 100\text{mA}, I_B = 5\text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{OBO}	—	3	—	pF	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Impedance	h_{ie}	—	4.5	—	K Ω	$V_{CE} = 5.0\text{V}, I_C = 2\text{mA}, f = 1.0\text{KHz}$
Voltage Feedback Ratio	h_{re}	—	2	—	$\times 10E-4$	
Small Signal Current Gain	h_{fe}	—	200	—	—	
Output Admittance	h_{oe}	—	30	—	μS	
Current Gain-Bandwidth Product	f_T	100	—	—	MHz	$V_{CE} = 20\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$
Noise Figure	NF	—	—	10	dB	$V_{CE} = 5\text{V}, I_C = 100\mu\text{A}, R_S = 1\text{K}\Omega, f = 1\text{kHz}$

Notes: 4. Short duration pulse test used to minimize self-heating effect.

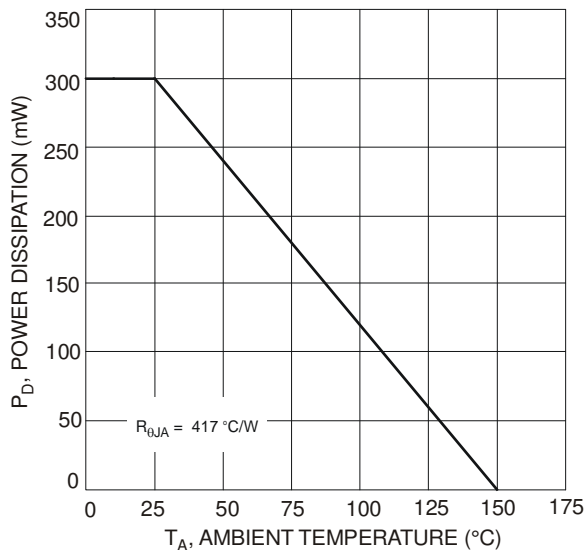


Fig. 1 Maximum Power Dissipation vs. Ambient Temperature

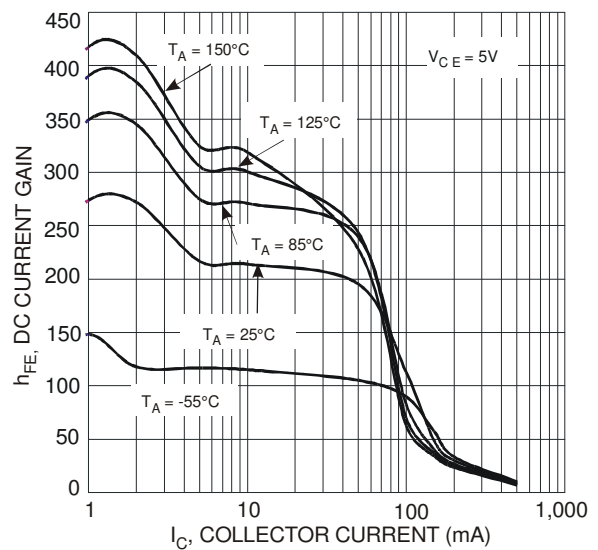


Fig. 2 Typical h_{FE} vs. I_C

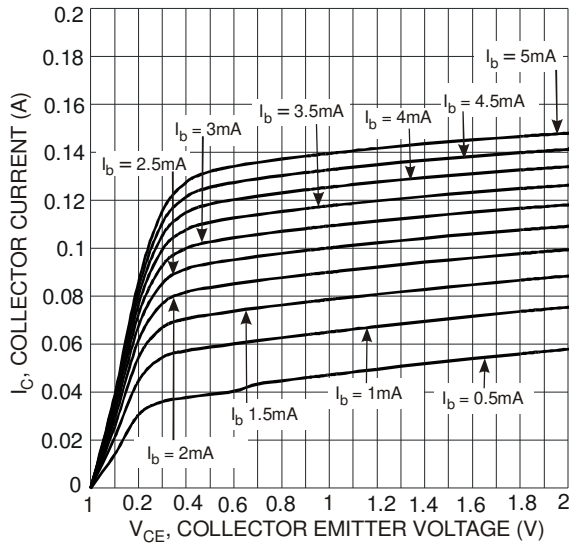


Fig. 3 Typical I_C vs. V_{CE}

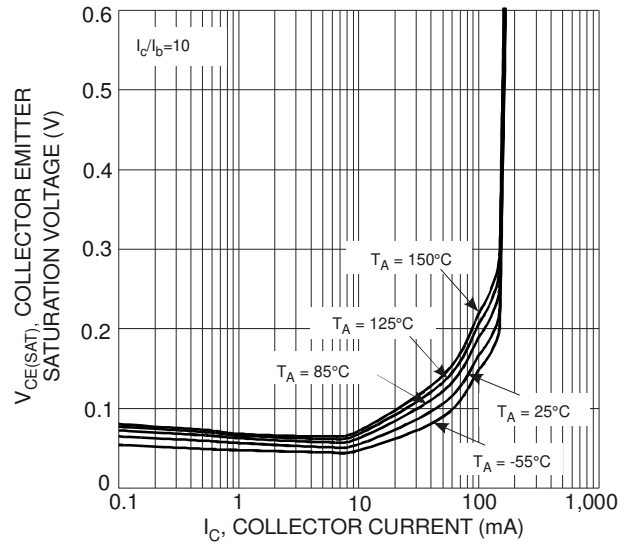


Fig. 4 Typical $V_{CE(SAT)}$ vs. I_C

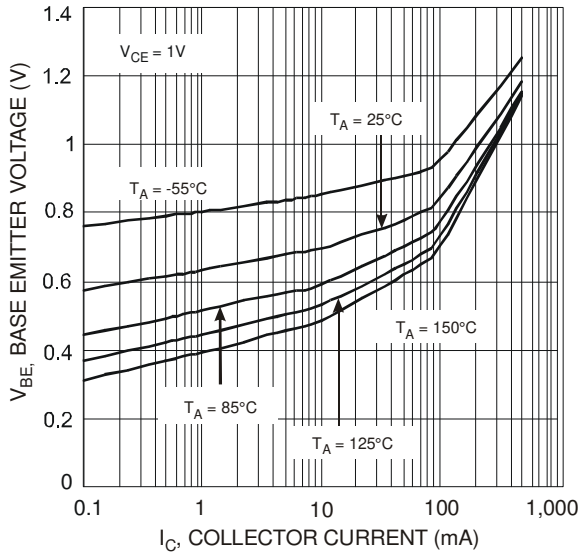


Fig. 5 Typical V_{BE} vs. I_C

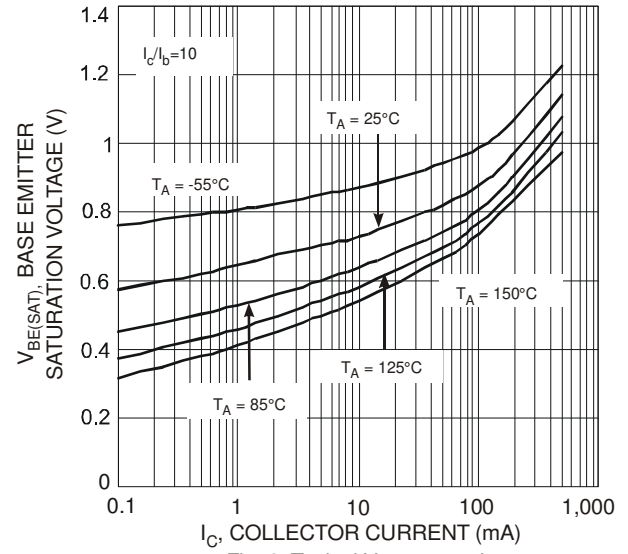


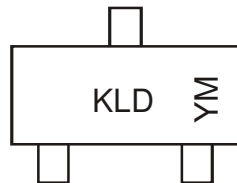
Fig. 6 Typical $V_{BE(SAT)}$ vs. I_C

Ordering Information (Note 5)

Device	Packaging	Shipping
BC847BLD-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

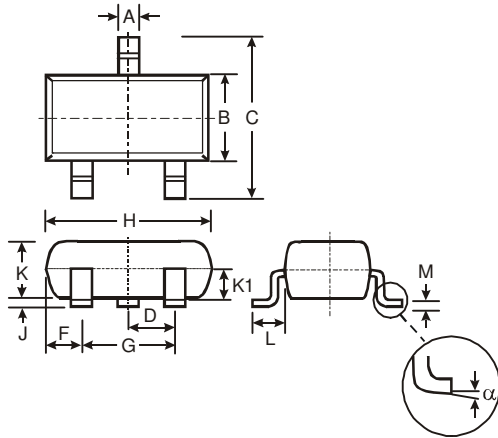


KLD = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: T = 2006
 M = Month ex: 9 = September

Date Code Key

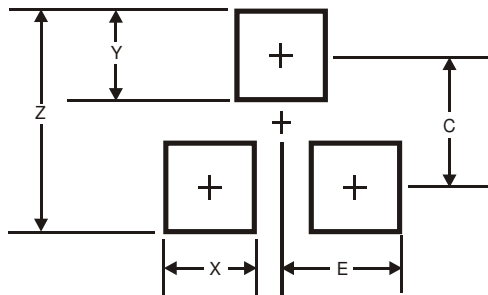
Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015		
Code	T	U	V	W	X	Y	Z	A	B	C		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Mechanical Details



SOT-23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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